ESDONCAN1, SESDONCAN1

CAN/CAN-FD Bus Protector

Low Capacitance ESD Protection Diode for CAN/CAN−FD Bus

The S/ESDONCAN1 has been designed to protect the CAN transceiver from ESD and other harmful transient voltage events. This device provides bidirectional protection for each data line with a single compact SOT−23 package, giving the system designer a low cost option for improving system reliability and meeting stringent EMI requirements.

Features

- 200 W Peak Power Dissipation per Line (8 x 20 μsec Waveform)
- Diode Capacitance Matching
- Low Reverse Leakage Current (< 100 nA)
- Low Capacitance High−Speed FlexRay Data Rates
- IEC Compatibility: − IEC 61000−4−2 (ESD): Level 4
  − IEC 61000−4−4 (EFT): 50 A – 5/50 ns
  − IEC 61000−4−5 (Lighting) 3.0 A (8/20 μs)
- ISO 7637−1, Nonrepetitive EMI Surge Pulse 2, 8.0 A (1 x 50 μs)
- ISO 7637−3, Repetitive Electrical Fast Transient (EFT) EMI Surge Pulses, 50 A (5 x 50 ns)
- Flammability Rating UL 94 V−0
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable
- These are Pb−Free Devices

Typical Applications

- Industrial
  - Smart Distribution Systems (SDS)
  - DeviceNet
- Automotive
  - Controlled Area Network − CAN 2.1 / CAN FD
  - Low and High Speed CAN

ON Semiconductor®

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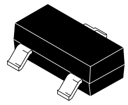
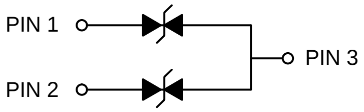
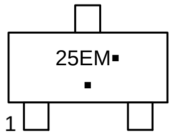
SOT−23
DUAL BIDIRECTIONAL
VOLTAGE SUPPRESSOR
200 W PEAK POWER



SOT−23
CASE 318
STYLE 27



MARKING DIAGRAM



25E = Device Code
M = Date Code
▪ = Pb−Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

MAXIMUM RATINGS (T_J = 25°C, unless otherwise specified)

Symbol	Rating	Value	Unit
PPK	Peak Power Dissipation, 8 x 20 μs Double Exponential Waveform (Note 1)	200	W
T_J	Operating Junction Temperature Range	−55 to 150	°C
T_J	Storage Temperature Range	−55 to 150	°C
T_L	Lead Solder Temperature (10 s)	260	°C
ESD	Human Body Model (HBM) Machine Model (MM) IEC 61000−4−2 Specification (Contact)	8.0 400 23	kV V kV

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Non−repetitive current pulse per Figure 1.

ELECTRICAL CHARACTERISTICS (T_J = 25°C, unless otherwise specified)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
V_{RWM}	Reverse Working Voltage	(Note 2)	24	−	−	V
V_{BR}	Breakdown Voltage	I_T = 1 mA (Note 3)	26.2	−	32	V
I_R	Reverse Leakage Current	V_{RWM} = 24 V	−	15	100	nA
V_C	Clamping Voltage	I_{PP} = 1 A (8 x 20 μs Waveform) (Note 4)	−	33.4	36.6	V
V_C	Clamping Voltage	I_{PP} = 3 A (8 x 20 μs Waveform) (Note 4)	−	44	50	V
I_{PP}	Maximum Peak Pulse Current	8 x 20 μs Waveform (Note 4)	−	−	3.0	A
C_J	Capacitance	V_R = 0 V, f = 1 MHz (Line to GND)	−	−	10	pF
ΔC	Diode Capacitance Matching	V_R = 0 V, 5 MHz (Note 5)	−	0.26	2	%

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. TVS devices are normally selected according to the working peak reverse voltage (V_{RWM}), which should be equal or greater than the DC or continuous peak operating voltage level.
3. V_{BR} is measured at pulse test current I_T.
4. Pulse waveform per Figure 1.
5. ΔC is the percentage difference between C_J of lines 1 and 2 measured according to the test conditions given in the electrical characteristics table.

ORDERING INFORMATION

Device	Package	Shipping†
ESDONCAN1LT1G	SOT−23 (Pb−Free)	3,000 / Tape & Reel
SESDONCAN1LT1G*	SOT−23 (Pb−Free)	3,000 / Tape & Reel
ESDONCAN1LT3G	SOT−23 (Pb−Free)	10,000 / Tape & Reel
SESDONCAN1LT3G*	SOT−23 (Pb−Free)	10,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable.

TYPICAL PERFORMANCE CURVES

(T_J = 25°C unless otherwise noted)

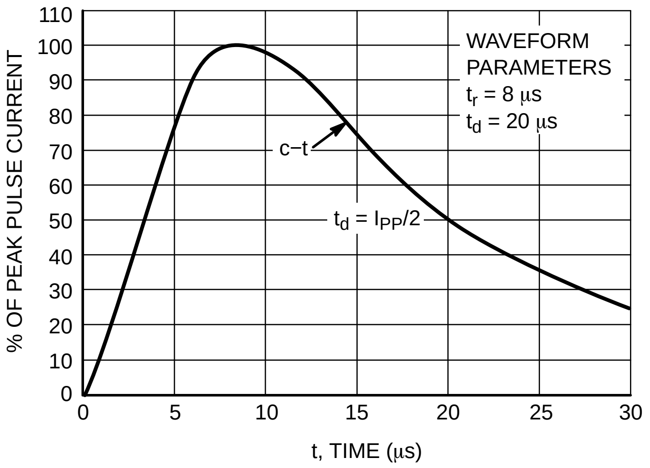


Figure 1. Pulse Waveform, 8 × 20 μs

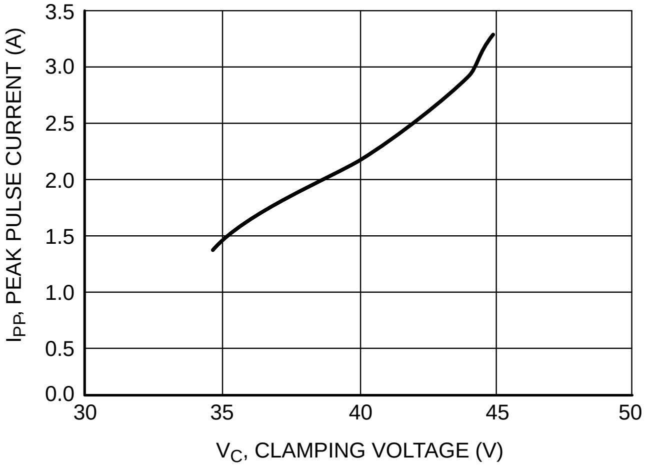


Figure 2. Clamping Voltage vs Peak Pulse Current

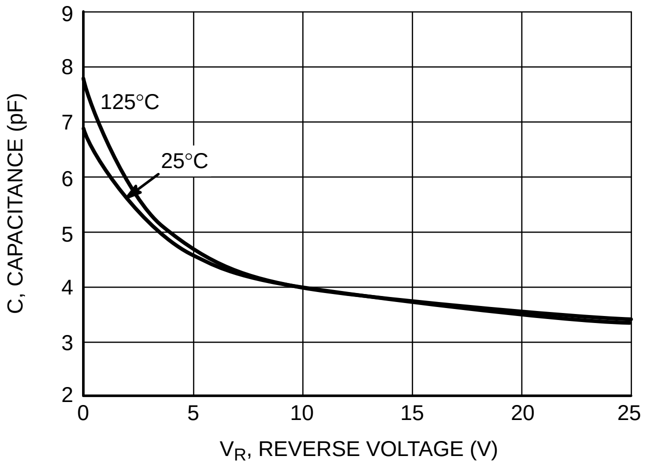


Figure 3. Typical Junction Capacitance vs Reverse Voltage

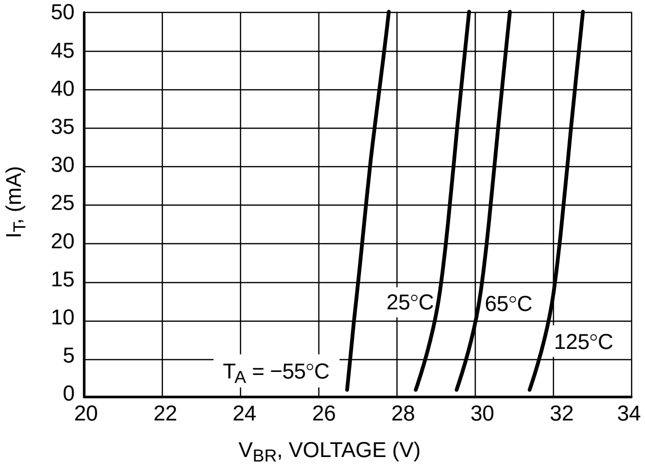


Figure 4. V_{BR} versus I_T Characteristics

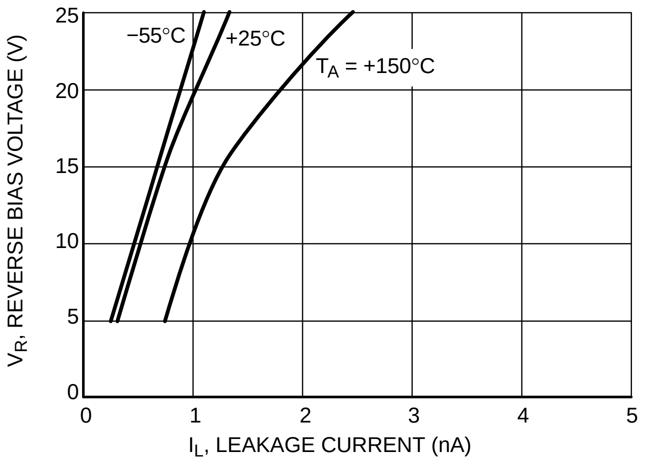


Figure 5. I_R versus Temperature Characteristics

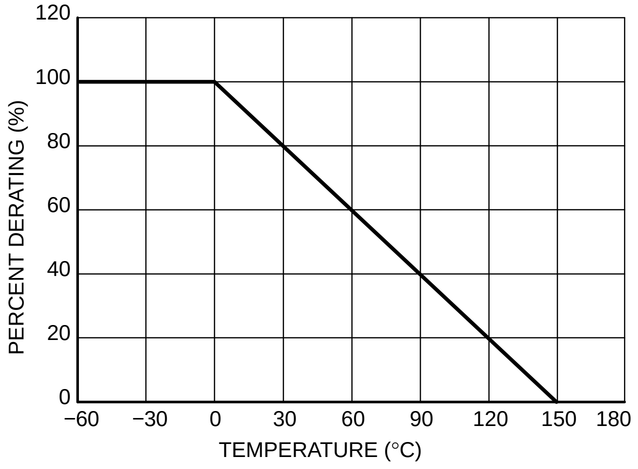


Figure 6. Temperature Power Dissipation Derating

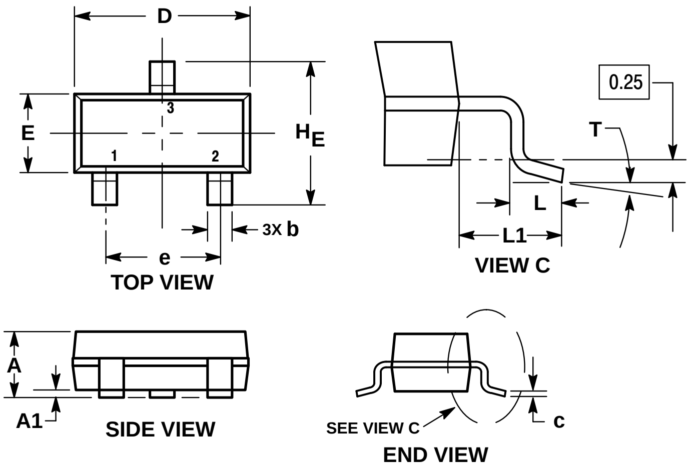
APPLICATIONS

Background

The Controller Area Network (CAN) is a serial communication protocol designed for providing reliable high speed data transmission in harsh environments. TVS diodes provide a low cost solution to conducted and radiated Electromagnetic Interference (EMI) and Electrostatic Discharge (ESD) noise problems. The noise immunity level and reliability of CAN transceivers can be easily increased by adding external TVS diodes to prevent transient voltage failures. The ESDONCAN1 provides a transient voltage suppression solution for CAN data communication lines. The ESDONCAN1 is a low capacitance dual bidirectional TVS device in a compact SOT-23 package especially suitable for CAN2.1 (CAN-FD). This device is based on Zener technology that optimizes the active area of a PN junction to provide robust protection against transient EMI surge voltage and ESD. The ESDONCAN1 has been tested to EMI and ESD levels that exceed the specifications of popular high speed CAN networks.

PACKAGE DIMENSIONS

SOT−23 (TO−236)
CASE 318−08
ISSUE AR

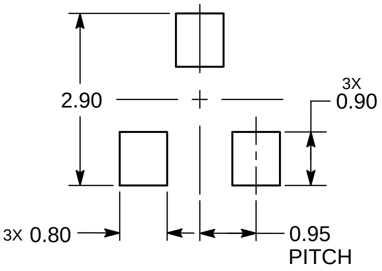


NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	**MIN**	**NOM**	**MAX**	**MIN**	**NOM**	**MAX**
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
H_E	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	−−−	10°	0°	−−−	10°

STYLE 27:
PIN 1. CATHODE
2. CATHODE
3. CATHODE

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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